

Sensors Unlimited: LDB/LSB Series



InGaAs linear photodiode arrays

Easy to use, analog LDB/LSB Series InGaAs photodiode arrays for high performance in NIR spectroscopy and imaging applications.

BENEFITS

- Easy-to-use analog design
- Wavelength ranges of 0.8 to 2.2 μm
- Pixel heights of 250 μm or 500 μm
- 25 μm or 50 μm pitch 1/2 and 1/4 inch array
- Two separate gains are selectable with a single input
- Maximum lps 1.25KHz analog output
- Anti-blooming to prevent charge overflow from saturated pixels
- Available with one- or two-stage thermoelectric cooler or without a cooler for uncooled or externally cooled operation
- ESD resistant

The LDB/LSB Series of linear InGaAs photodiode arrays are ideal for monitoring optical performance across S, C, and L band channels in DWDM networks. They also serve in diverse applications such as agricultural sorting, biomedical analysis, thermal imaging, and industrial process control.

The LDB/LSB series are available with options of 256 and 512 elements, available on either a 25 μ m or 50 μ m pixel pitch, and with pixel heights of 250 μ m and 500 μ m. The arrays support various wavelength ranges: a standard range of 0.8 to 1.7 μ m, a shorter range of 0.8 to 1.45 μ m, or an extended range of 1.1 to 2.2 μ m. These photodetector arrays are integrated with SUI's proprietary CMOS readout integrated circuits (ROIC), designed to maximize noise immunity and sensitivity.

Operating these arrays requires minimal circuitry, with only one analog supply and two digital control lines needed for optimal ROIC performance. The arrays offer selectable gains through a single input. Optionally, they can be equipped with thermoelectric coolers for temperature stabilization and monitoring.

Applications

- Optical performance monitoring of S, C and L band channels in DWDM networks
- Agricultural sorting
- Biomedical analysis
- Thermal imaging
- Industrial process control
- Spectroscopy
- Telecommunications

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Parameter/description	Unit	Min.	Typical	Max.
V _{DD} /analog supply voltage	V	4.90	5.00	5.25
Vss/analog supply ground	V		0	
V _{PP} /amplifier dead potential	V		3.25	
Vclk/digital pixel clock	V		Hi: Vdd Low: Vss	
VLSYNC/digital exposure control	V		Hi: Vdd Low: Vss	
Vcap/digital gain control	V		Hi: Vdd Low: Vss	

Electrical inputs

Absolute maximum ratings

Parameter/description		Unit	Min.	Typical	Max.
Power consumption (V _{DD} =5.00 V)	LDB LSB	mW mW			300 150
Operating temperature range		°C	-20		+70
Storage temperature range		°C	-40		+85

Linear array comparison table (representative values)

Material type	Dark current	50% QE cut-on λ (μm)	50% QE cut-off λ (μm)	Peak λ (μm)
1.45 µm	1.3 pA	0.91	1.415	1.17
1.7 μm	2.3 pA	0.91	1.65	1.36
2.2 µm	10 nA	1.3	2.155	1.67
2.6 µm	100 nA	1.64	2.41	1.84



Performance characteristics

Parameter	Unit	Min.	Typical	Max.
Peak wavelength sensitivity (λpk)	μm		1.5	
Responsivity (at λpk)	nV/ photon	10.5		
Photoresponse nonuniformity (PRNU)	%		5	10
Gain	nV/ electron		4.00 ¹ , 15.4 ²	
Saturation charge	pC		0.8 ¹ , 20.8 ²	
Readout noise	Electron/ √scan		800 ¹ , 10,000 ²	
Pixel clock	MHz			1.25
Readout rate per output	Mpix/ sec/ output			2.5
Inoperable pixels	%			0

¹High-sensitivity mode: high gain capacitor. ²High-dynamic range mode: low gain capacitor.

Contact

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Specifications subject to change without notice.

